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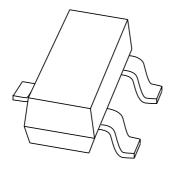
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BCW61 seriesPNP general purpose transistors

Product data sheet Supersedes data of 1997 May 28 1999 Apr 12



NXP Semiconductors Product data sheet

PNP general purpose transistors

BCW61 series

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 32 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complement: BCW60.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW61B	BB*
BCW61C	BC*
BCW61D	BD*

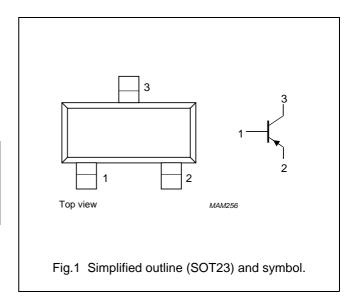
Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

LIMITING VALUES

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-32	V
V_{CEO}	collector-emitter voltage	open base	_	-32	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

1999 Apr 12 2

NXP Semiconductors Product data sheet

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -32 \text{ V}$	_	_	-20	nA
		$I_E = 0$; $V_{CB} = -32 \text{ V}$; $T_{amb} = 150 ^{\circ}\text{C}$	_	_	-20	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -4 \text{ V}$	_	_	-20	nA
h _{FE}	DC current gain	$I_C = -10 \mu A; V_{CE} = -5 V$				
	BCW61B		30	_	_	
	BCW61C		40	_	_	
	BCW61D		100	_	_	
	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$				
	BCW61B		180	_	310	
	BCW61C		250	_	460	
	BCW61D		380	_	630	
	DC current gain	$I_C = -50 \text{ mA}; V_{CE} = -1 \text{ V}$				
	BCW61B		80	_	_	
	BCW61C		100	_	_	
	BCW61D		110	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.25 \text{ mA}$	-60	_	-250	mV
		$I_C = -50 \text{ mA}; I_B = -1.25 \text{ mA}$	-120	_	-550	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.25 \text{ mA}$	-600	_	-850	mV
		$I_C = -50 \text{ mA}; I_B = -1.25 \text{ mA}$	-0.68	_	-1.05	V
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}$; $V_{CE} = -5 \text{ V}$	-600	-650	-750	mV
		$I_C = -10 \ \mu A; \ V_{CE} = -5 \ V$	_	-550	_	mV
		$I_C = -50 \text{ mA}; V_{CE} = -1 \text{ V}$	_	-720	_	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	4.5	_	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = -0.5 \text{ V}$; $f = 1 \text{ MHz}$	_	11	_	pF
f _T	transition frequency	$I_C = -10$ mA; $V_{CE} = -5$ V; $f = 100$ MHz; note 1	100	_	_	MHz
F	noise figure	$\begin{split} I_C = -200 \; \mu A; V_{CE} = -5 \; V; R_S = 2 \; k\Omega; \\ f = 1 \; kHz; \; B = 200 \; Hz \end{split}$	_	2	6	dB

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

1999 Apr 12 3

NXP Semiconductors Product data sheet

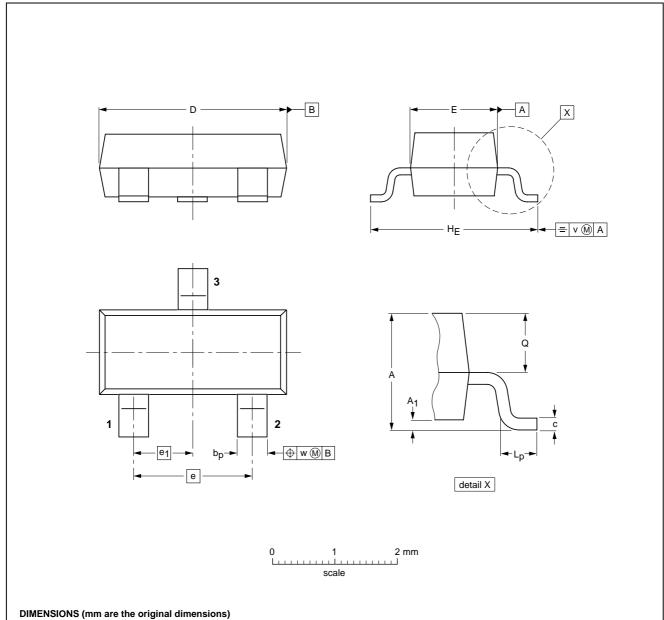
PNP general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				97-02-28 99-09-13

1999 Apr 12 4 NXP Semiconductors Product data sheet

PNP general purpose transistors

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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1999 Apr 12 5

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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